

# **10W AUDIO AMPLIFIER WITH MUTING**

### DESCRIPTION

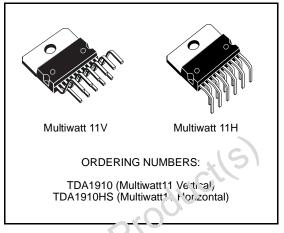
The TDA 1910 is a monolithic integrated circuit in MULTIWATT® package, intended for use in Hi-Fi audio power applications, as high quality TV sets. The TDA 1910 meets the DIN 45500 (d = 0.5%) guaranteed output power of 10W when used at 24V/4W. At 24V/8W the output power is 7W min. Features:

- muting facility
- protection against chip over temperature
- very low noise
- high supply voltage rejection
- low "switch-on" noise.

The TDA 1910 is assembled in MULTIWATT® package that offers:

- easy assembly
- simple heatsink

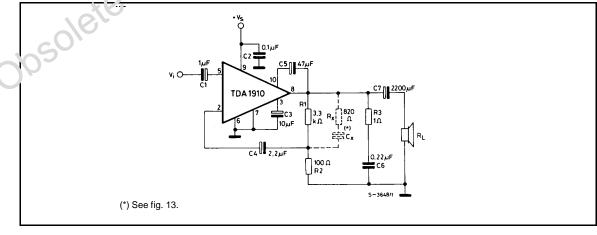
### **ABSOLUTE MAXIMUM RATINGS**



- space and cost saving
- high reliab."ity

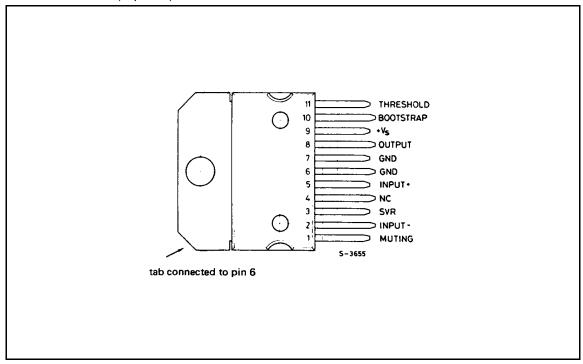
Symbol	Parameter	Value	Unit
Vs	Supply voltage	30	V
lo	Output peak current (non repetitive)	3.5	А
lo	Output peak current (repetitive)	3.0	А
Vi	Input voltage	$0 \text{ to } + \text{V}_{\text{s}}$	V
Vi	Differential input voltage	± 7	V
V <sub>11</sub>	Muting thresold voltage	Vs	V
Ptot	Power dissipation $et T_{u_{1}se} = 90^{\circ}C$	20	W
T <sub>stg</sub> , T <sub>j</sub>	Storage and junction temperature	-40 to 150	°C

### **TEST CIRCUIT**

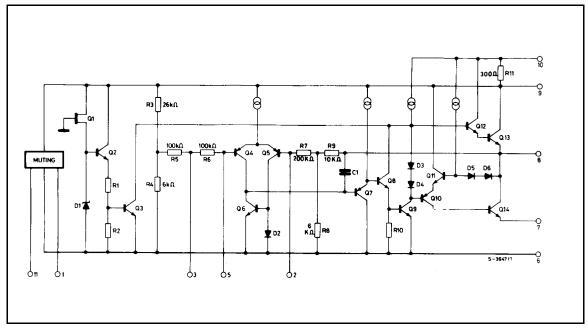


#### September 2003

# **PIN CONNECTION** (Top view)

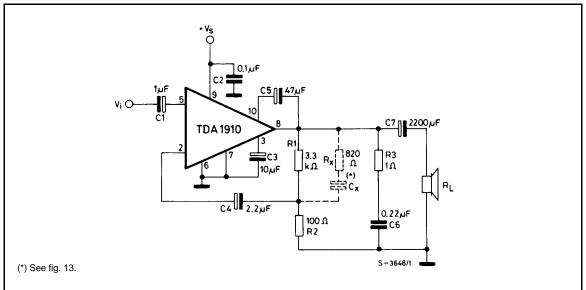


### SCHEMATIC DIAGRAM

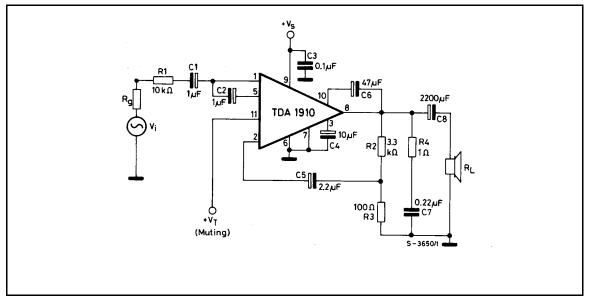


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### **TEST CIRCUIT**



### **MUTING CIRCUIT**



### THERMAL DATA

Symbol	Parameter	Value	Unit
R <sub>th j-case</sub>	Thermal resistance junction-case max	3	°C/W

# **ELECTRICAL CHARACTERISTICS** (Refer to the test circuit, $T_{amb} = 25 \text{ °C}$ , $R_{th}$ (heatsink) = 4°C/W, unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
Vs	Supply voltage		8		30	V
Vo	Quiescent output voltage	$V_s = 18V$ $V_s = 24V$	8.3 11.5	9.2 12.4	10 13.4	V
l <sub>d</sub>	Quiescent drain current	$V_s = 18V$ $V_s = 24V$		19 21	32 35	mA
V <sub>CE sat</sub>	Output stage saturation voltage	I <sub>C</sub> = 2A		1		V
		I <sub>C</sub> = 3A		1.6		•
Po	Output power	$\begin{array}{ll} d = 0.5\% & f = 40 \ to \ 15,000 \text{Hz} \\ V_{\text{S}} = 18V & \text{R}_{\text{L}} = 4\Omega \\ V_{\text{S}} = 24V & \text{R}_{\text{L}} = 4\Omega \\ V_{\text{S}} = 24V & \text{R}_{\text{L}} = 8\Omega \end{array}$	6.5 10 7	7 12 7.5		V
		$ \begin{array}{ll} d = 10\% & f = 1 \; KHz \\ V_{s} = 18V & R_{L} = 4\Omega \\ V_{s} = 24V & R_{L} = 4\Omega \\ V_{s} = 24V & R_{L} = 8\Omega \end{array} $	8.5 15 9	9.5 17 10		
d	Harmonic distortion	$ \begin{array}{l} f = 40 \ to \ 15,000 \ Hz \\ V_s = 18V \\ P_o = 50 \ mW \ to \ 6.5W \\ V_s = 24V \\ R_L = 4\Omega \\ P_o = 50 \ mW \ to \ 10W \\ V_s = 24V \\ R_L = 8\Omega \\ P_o = 50 \ mW \ to \ 7W \end{array} $		0.2 0.2 0.2	0.5 0.5 0.5	%
d	Intermodulation distortion	$ \begin{array}{ll} V_{s} = 24V & R_{L} = 4\Omega & P_{o} = 10W \\ f_{1} = 250 \ Hz & f_{2} = 8 \ KHz \\ & (DIN \ 45500) \end{array} $		0.2		%
Vi	Input sensitivity	$ \begin{array}{ll} F = 1 \ KHz, \\ V_s = 18V \\ v_s = 24V \\ V_s = 24V \\ V_s = 24V \\ \end{array} \begin{array}{ll} R_L = 4\Omega \\ R_L = 4\Omega \\ R_L = 8\Omega \\ P_o = 7.5W \end{array} $		170 220 245		mV
Vi	Input saturation voltage (rms)	$V_s = 18V$ $V_s = 24V$	1.8 2.4			V
R <sub>i</sub>	Input resistance (pin 5)	f = 1 KHz	60	100		KΩ
ld	Drain current	$ \begin{array}{ll} V_{S} = 24V & f = 1 \ KHz \\ R_{L} = 4\Omega & P_{o} = 12W \\ RL = 8\Omega & P_{o} = 7.5W \end{array} $		820 475		mA

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Symbol	Parameter	Tes	st condition		Min.	Тур.	Max.	Unit
h	Efficiency	$V_{s} = 24V$ $R_{L} = 49$ $R_{L} = 89$	$f = 1 \text{ KH}$ $\Omega \qquad P_0 =$ $\Omega \qquad P_0 =$	lz = 12W = 7.5W		62 65		%
BW	Small signal bandwidth	$V_s = 24V$	$R_L = 4\Omega$ F	$P_o = 1W$	10	to 120,0	00	Hz
BW	Power bandwidth	$V_s = 24V$ $P_o = 12W$	$\begin{array}{l} R_{L}=4\Omega\\ d\leq 5\% \end{array}$		40	) to 15,00	00	Hz
Gv	Voltage gain (open loop)	f = 1 KHz				75		dB
Gv	Voltage gain (closed loop)	V <sub>s</sub> = 24V f = 1 KHz	$R_L = 4\Omega$ Po = 1W		29.5	30	30.5	dB
e <sub>N</sub>	Total input noise		$\begin{array}{l} R_{g} = 50\Omega \\ R_{g} = \ 1K\Omega \\ R_{g} = \ 10K\Omega \end{array}$	(°)		1.2 1.3 1.5	3.0 3.2 4.0	μV
			$\begin{array}{l} R_{g} = 50\Omega \\ R_{g} = \ 1K\Omega \\ R_{g} = \ 10K\Omega \end{array}$	(°°)		2.0 2.0 2.2	5.0 5.2 6.0	μV
S/N	Signal to noise ratio	$V_s = 24V$ $P_o = 12W$	$\begin{array}{l} R_{g} = 10K\Omega\\ R_{g} = 0 \end{array}$	(°)	97	103 105		dB
		$R_L = 4\Omega$	$\begin{array}{l} R_{g} = 10K\Omega\\ R_{g} = 0 \end{array}$	(°°)	93	100 100		dB
SVR	Supply voltage rejection	$V_{s} = 24V \qquad RL = 4\Omega$ f <sub>ripple</sub> = 100 Hz \qquad Rg = 10 K\Omega			50	60		dB
T <sub>sd</sub>	Thermal sjut-down case (*) temperature		$P_{tot} = 8W$		110	125		°C

## ELECTRICAL CHARACTERISTICS (continued)

## MUTING FUNCTION (Refer to Muting circuit)

VT	Muting-off threshold voltage (pin 11)		1.9		4.7	V
VT	Muting-on threshold voltage		0		1.3	V
	(pin 11)		6		Vs	
R <sub>1</sub>	Input resistance (pin 1)	Muting off	80	200		KΩ
		Muting on		10	30	Ω
R <sub>11</sub>	Input resistance (pin 11)		150			KΩ
A <sub>T</sub>	Muting attenuation	$R_g + R_1 = 10 \text{ K}\Omega$	50	60		dB

Note : (°) Weighting filter = curve A. (°°) Filter with noise bandwidth: 22 Hz to 22 KHz. (\*) See fig. 29 and fig. 30.

# Figure 1. Quiescent output voltage vs. supply voltage

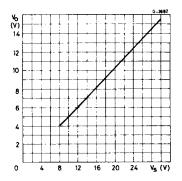
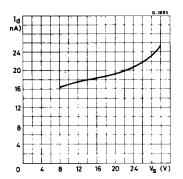


Figure 2. Quiescent drain current vs. supply voltage



#### Figure 3. Open loop frequency response

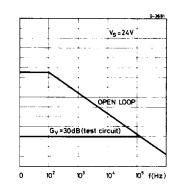


Figure 4. Output power vs. supply voltage

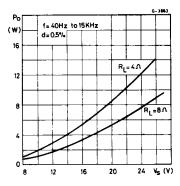


Figure 5. Output power vs. supply voltage

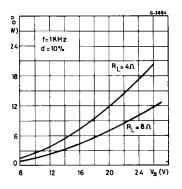
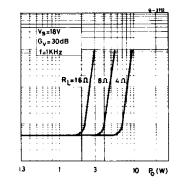


Figure 6. Distortion vs. output power



# Figure 7. Distortion vs. output power

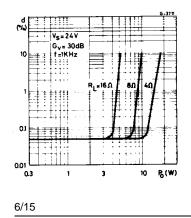


Figure 8. Output power vs. frequency

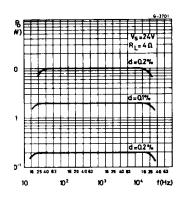


Figure 9. Output power vs. frequency

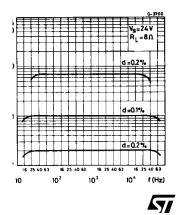


Figure 10. Output power vs. input voltage

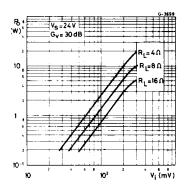
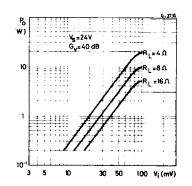


Figure 11. Output power vs. input voltage



# Figure 12. Total input noise vs. source resistance

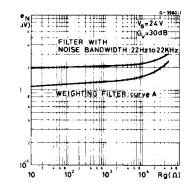


Figure 13. Values of capacitor Cx vs. bandwidth (BW) and gain (G $_V$ )

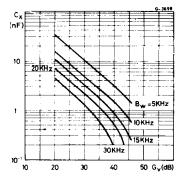


Figure 14. Supply voltage rejection vs. voltage gain

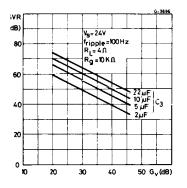


Figure 15. Supply voltage rejection vs. source resistance

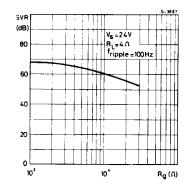


Figure 16. Power dissipation and efficiency vs. output power

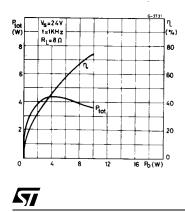


Figure 17. Power dissipation and efficiency vs. output power

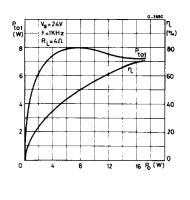
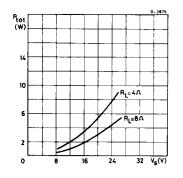


Figure 18. Max power dissipation vs. supply voltage





# **APPLICATION INFORMATION**

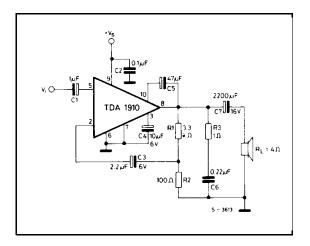


Figure 21. Application circuit with muting

0.22 µF

.V<sub>T</sub> Muting

-

II C3

<u></u> 0.1μF

TDA 1910

C7 47,uF

C6 6V

3.3 kΩ[]R2

100 ቧ R3 C9 2200, F

RL=4Ω

]R4 1Ω

0.22 µF C 8

S-3612

C

-0

20 k Ω.

Vol

R1

3.3kΩ 1µF

# Figure 19. Application circuit without muting

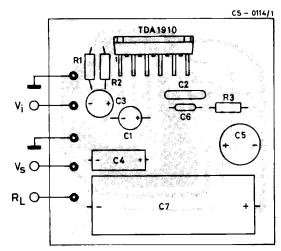
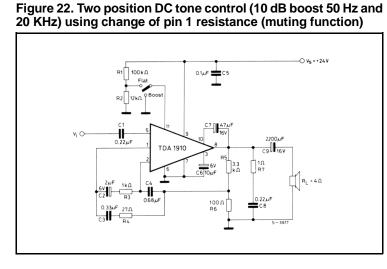


Figure 20. PC board and component lay-out of the circuit of fig. 19 (1:1 scale)

 $\begin{array}{l} \mbox{Performance (circuits of fig. 19 and 21)} \\ \mbox{P}_o = 12W~(40~to~15000~Hz,~d \leq 0.5\%) \\ \mbox{V}_s = 24V \\ \mbox{I}_d = 0.82A \\ \mbox{G}_v = 30~dB \end{array}$ 



## **APPLICATION INFORMATION (continued)**



#### Figure 23. Frequency response of the circuit of fig. 22

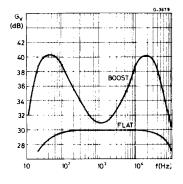


Figure 24. 10 dB 50 Hz boos tone control using change of pin 1 resistance (muting function)

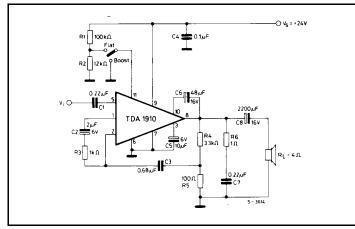


Figure 25. Frequency response of the circuit of fig. 24

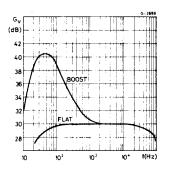
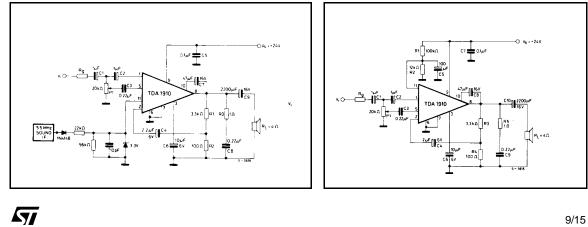


Figure 27. Delayed muting circuit

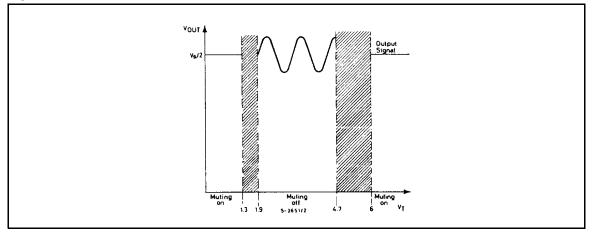




### **MUTING FUNCTION**

The output signal can be inhibited applying a DC voltage VT to pin 11, as shown in fig. 28

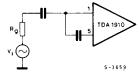
### Figure 28

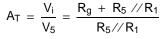


The input resistance at pin 1 depends on the threshold voltage V<sub>T</sub> at pin 11 and is typically.

$R_1 = 200 \text{ K}\Omega$	@	$1.9V \le V_T \le 4.7V$	muting-off
$R1 = 10 \Omega$	@	$0V \le V_T \le 1.3V$ $6V \le V_T \le V_s$	muting-on

Referring to the following input stage, the possible attenuation of the input signal and therefore of the output signal can be found using the following expression.





where  $R5 \cong 100 \text{ K}\Omega$ 

Considering Rg = 10 K $\Omega$  the attenuation in the muting-on condition is typically A<sub>T</sub> = 60 dB. In the muting-off condition, the attenuation is very low, typically 1.2 dB.

A very low current is necessary to drive the threshold voltage  $V_T$  because the input resistance at pin 11 is greater than 150 K $\Omega$ . The muting function can be used in many cases, when a temporary inhibition of the output signal is requested, for example:

- in switch-on condition, to avoid preamplifier power-on transients (see fig. 27)

- during commutations at the input stages.

- during the receiver tuning.

The variable impedance capability at pin 1 can be useful in many applications and we have shown 2 examples in fig. 22 and 24, where it has been used to change the feedback network, obtaining 2 different frequency responses.

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# APPLICATION SUGGESTION

The recommended values of the components are those shown on application circuit of fig. 21. Different values can be used. The following table can help the designer.

Component	Raccom.	Plirboso	Larger than	Smaller than	Allowed range		
•••••p•••••	value		recommended value	recommended value	Min.	Max.	
R <sub>g</sub> + R <sub>1</sub>	10KΩ	Input signal imped. for muting operation	Increase of the atte- nuation in muting-on condition. Decrease of the input sensitivity.	Decrease of the attenuation in muting on condition.			
R <sub>2</sub>	3.3KΩ	Close loop gain setting.	Increase of gain.	Decrease of gain. Increase quiescent current.	9 R <sub>3</sub>		
R <sub>3</sub>	100Ω	Close loop gain setting.	Decrease of gain.	Increase of gain.		R <sub>2</sub> /9	
R4	1Ω	Frequency stability	Danger of oscillation at high frequencies with inductive loads.				
P <sub>1</sub>	20ΚΩ	Volume potentiometer.	Increase of the switch-on noise.	Decrease of the input impedance and of the input level.	10KΩ	100KΩ	
$egin{array}{c} C_1 \ C_2 \ C_3 \end{array}$	1 μF 1 μF 0.22μF	Input DC decoupling.		Higher low frequency cutoff.			
C <sub>4</sub>	2.2μF	Inverting input DC decoupling.	Increase of the switch-on noise.	Higher low frequency cutoff.	0.1µF		
C <sub>5</sub>	0.1µF	Supply voltage bypass.		Danger of oscillations.			
C <sub>6</sub>	10µF	Ripple rejection.	Increase of SVR. Increase of the switch-on time	Degradation of SVR	2.2μF	100µF	
C <sub>7</sub>	47μF	Bootstrap.		Increase of the distor- tion at low frequency.	10μF	100µF	
C <sub>8</sub>	0.22µF	Frequency stability.		Danger of oscillation.			
C <sub>9</sub>	$\begin{array}{c} 2200 \mu F \\ (R_L = 4 \Omega) \\ 1000 \ \mu F \\ (R_L = 8 \Omega) \end{array}$	Output DC decoupling.		Higher low frequency cutoff.			

R

12

10

0

(₩

### THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily supported since the T<sub>j</sub> cannot be higher than 150°C.
- 2) The heatskink can have a smaller factor of safety compared with that of a conventional

ч

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Tcase(\*C)

circuit. There is no possibility of device damage due to high junction temperature.

If for any reason, the junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation and the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 31 shows this dissipable power as a function of ambient temperature for different thermal resistance.

# Figure 29. Output power and drain current vs. case temperature

R

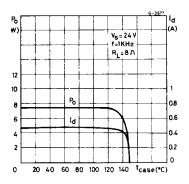
id

20 40 60 80 100 120 140

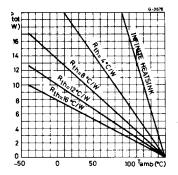
V<sub>S</sub>=24V f = 1KHz

RL=4∩

Figure 30. Output power and drain current vs. case temperature



#### Figure 31. Maximum allow able power dissipation vs. ambient temperature



### MOUNTING INSTRUCTIONS

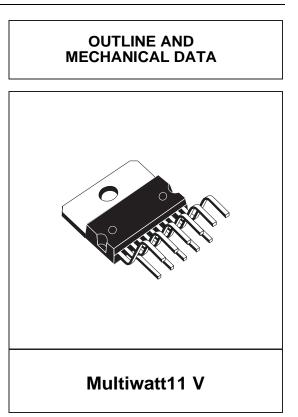
The power dissipated in the circuit must be removed by adding an external heatsink.

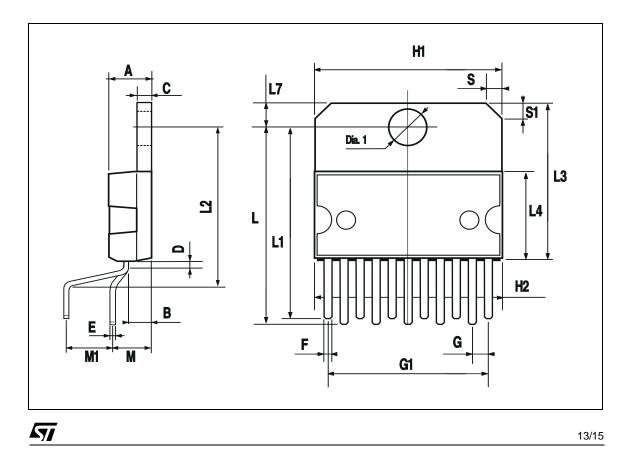
Thanks to the Multiwatt® package attaching the heatsink is very simple, a screw or a compression

spring (clip) being sufficient. Between the heatsink and the package it is better to insert a layer of silicon grease, to optimize the thermal contact; no electrical isolation is needed between the two surfaces.

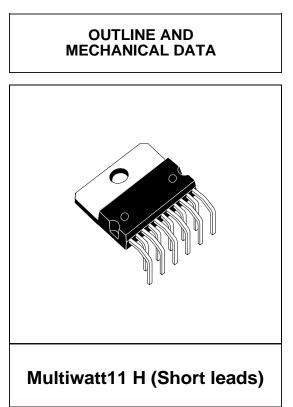


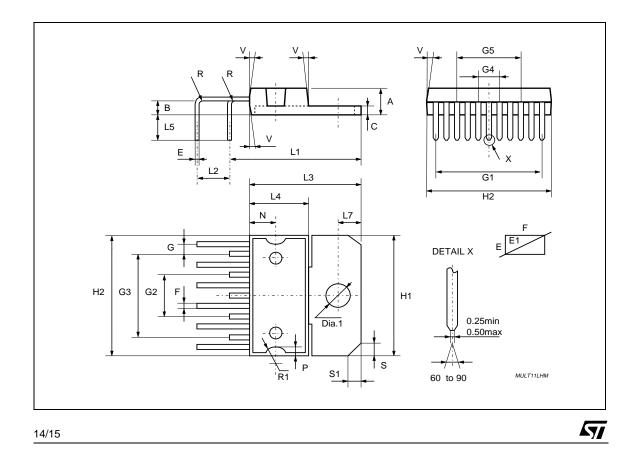
DIM.		mm			inch	
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			5			0.197
В			2.65			0.104
С			1.6			0.063
D		1			0.039	
Е	0.49		0.55	0.019		0.022
F	0.88		0.95	0.035		0.037
G	1.45	1.7	1.95	0.057	0.067	0.077
G1	16.75	17	17.25	0.659	0.669	0.679
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.87	0.886
L2	17.4		18.1	0.685		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
М	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.73	5.08	5.43	0.186	0.200	0.214
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152





DIM.		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.373	4.5	4.627	0.172	0.177	0.182
В			2.65			0.104
С			1.6			0.063
Е	0.49	0.515	0.55	0.019	0.020	0.022
E1	1.007	1.037	1.07	0.040	0.041	0.042
F	0.88	0.9	0.95	0.035	0.035	0.037
G	1.5	1.7	1.9	0.059	0.067	0.075
G.1	16.82	17.02	17.22	0.662	0.670	0.678
G2	6.61	6.807	7.01	0.260	0.268	0.276
G3	13.41	13.61	13.81	0.528	0.536	13.810
G4	3.2	3.4	3.6	0.126	0.134	0.142
G5	10.01	10.21	10.41	0.394	0.402	0.410
H1	19.6			0.772		
H2			20.2			0.795
L1	19.28	19.58	19.88	0.759	0.771	0.783
L2	3.61	3.81	4.01	0.142	0.150	0.158
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.6	10.9	0.406	0.417	0.429
L5 (Inner)	3.4	3.75	4	0.134	0.148	0.157
L5 (Outer)	3.6	3.9	4.2	0.142	0.154	4.200
L7	2.65		2.9	0.104		0.114
R	0.75	1	1.25	0.030	0.039	0.049
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152





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